

## 30V, N-Channel NexFET™ Power MOSFETs

Check for Samples: [CSD17506Q5A](#)

### FEATURES

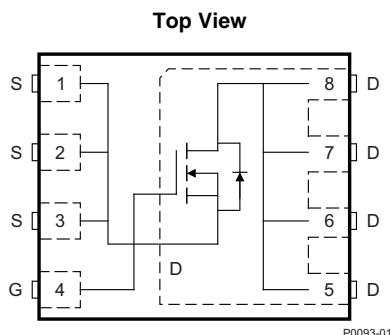
- **Ultralow  $Q_g$  and  $Q_{gd}$**
- **Low Thermal Resistance**
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- **SON 5-mm × 6-mm Plastic Package**

### APPLICATIONS

- **Point-of-Load Synchronous Buck in Networking, Telecom, and Computing Systems**
- **Synchronous or Control FET Applications**

### DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.



### PRODUCT SUMMARY

$T_A = 25^\circ\text{C}$ unless otherwise stated		TYPICAL VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	30	V
$Q_g$	Gate Charge Total (4.5V)	8.3	nC
$Q_{gd}$	Gate Charge Gate to Drain	2.3	nC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 4.5\text{V}$	4.2 mΩ
		$V_{GS} = 10\text{V}$	3.2 mΩ
$V_{GS(th)}$	Threshold Voltage	1.3	V

### ORDERING INFORMATION

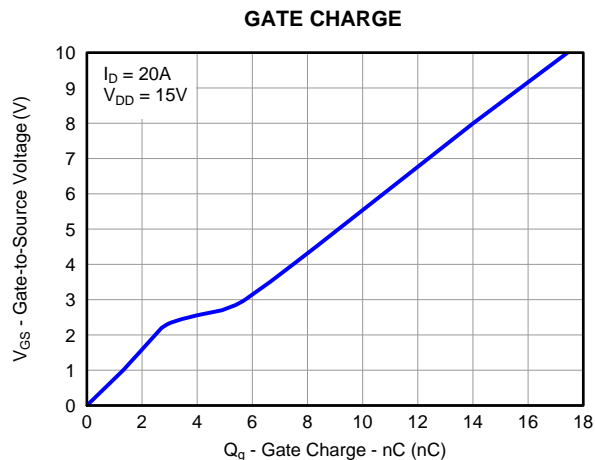
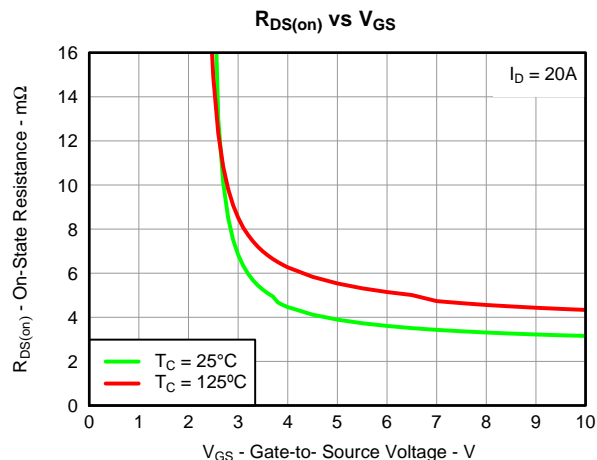
Device	Package	Media	Qty	Ship
CSD17506Q5A	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

### ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ unless otherwise stated		VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	±20	V
$I_D$	Continuous Drain Current, $T_C = 25^\circ\text{C}$	100	A
	Continuous Drain Current <sup>(1)</sup>	23	A
$I_{DM}$	Pulsed Drain Current, $T_A = 25^\circ\text{C}$ <sup>(2)</sup>	150	A
$P_D$	Power Dissipation <sup>(1)</sup>	3.2	W
$T_J$ , $T_{STG}$	Operating Junction and Storage Temperature Range	–55 to 150	°C
$E_{AS}$	Avalanche Energy, single pulse $I_D = 72\text{A}$ , $L = 0.1\text{mH}$ , $R_G = 25\Omega$	259	mJ

(1) Typical  $R_{\theta JA} = 39^\circ\text{C/W}$  on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration ≤300μs, duty cycle ≤2%



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## ELECTRICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

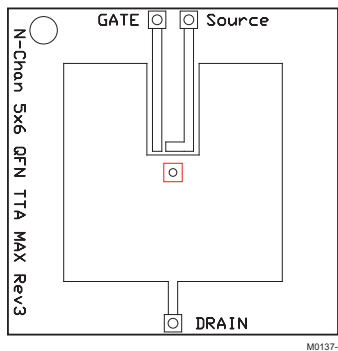
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
B <sub>DSS</sub>	Drain to Source Voltage	V <sub>GS</sub> = 0V, I <sub>DS</sub> = 250μA	30			V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 24V			1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 20V			100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> = 250μA	1	1.3	1.8	V
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 4.5V, I <sub>DS</sub> = 20A	4.2		5.3	mΩ
		V <sub>GS</sub> = 10V, I <sub>DS</sub> = 20A	3.2		4	mΩ
g <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15V, I <sub>DS</sub> = 20A	76			S
Dynamic Characteristics						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 15V, f = 1MHz	1270		1650	pF
C <sub>oss</sub>	Output Capacitance		860		1120	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		50		65	pF
R <sub>G</sub>	Series Gate Resistance		1.1		2.2	Ω
Q <sub>g</sub>	Gate Charge Total (4.5V)	V <sub>DS</sub> = 15V, I <sub>DS</sub> = 20A	8.3		11	nC
Q <sub>gd</sub>	Gate Charge Gate to Drain		2.3			nC
Q <sub>gs</sub>	Gate Charge Gate to Source		3.1			nC
Q <sub>g(th)</sub>	Gate Charge at V <sub>th</sub>		1.6			nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 14V, V <sub>GS</sub> = 0V	23			nC
t <sub>d(on)</sub>	Turn On Delay Time	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>DS</sub> = 20A, R <sub>G</sub> = 2Ω	7.5			ns
t <sub>r</sub>	Rise Time		13			ns
t <sub>d(off)</sub>	Turn Off Delay Time		13			ns
t <sub>f</sub>	Fall Time		5.3			ns
Diode Characteristics						
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> = 20A, V <sub>GS</sub> = 0V	0.8		1	V
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>DD</sub> = 14V, I <sub>F</sub> = 20A, di/dt = 300A/μs	33			nC
t <sub>rr</sub>	Reverse Recovery Time		27			ns

## THERMAL CHARACTERISTICS

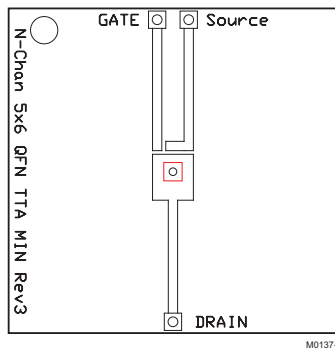
( $T_A = 25^\circ\text{C}$  unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			1	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>(1)(2)</sup>			50	$^\circ\text{C/W}$

- (1)  $R_{\theta JC}$  is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB.  $R_{\theta JC}$  is specified by design, whereas  $R_{\theta JA}$  is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.



Max  $R_{\theta JA} = 50^{\circ}\text{C/W}$   
when mounted on  
1 inch<sup>2</sup> (6.45 cm<sup>2</sup>) of 2-  
oz. (0.071-mm thick)  
Cu.



Max  $R_{\theta JA} = 120^{\circ}\text{C/W}$   
when mounted on a  
minimum pad area of  
2-oz. (0.071-mm thick)  
Cu.

## TYPICAL MOSFET CHARACTERISTICS

( $T_A = 25^{\circ}\text{C}$  unless otherwise stated)

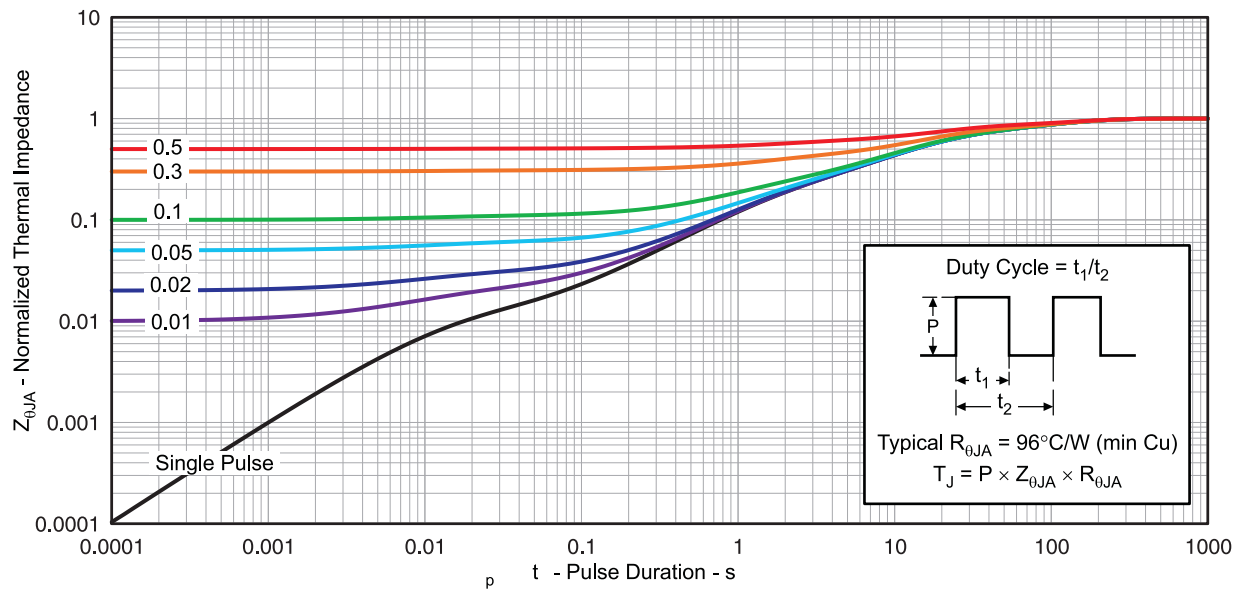
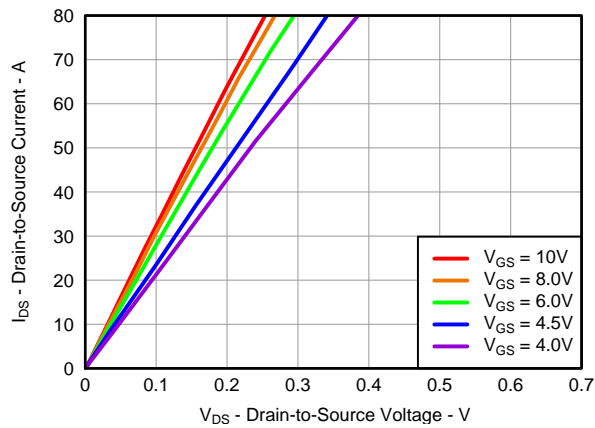


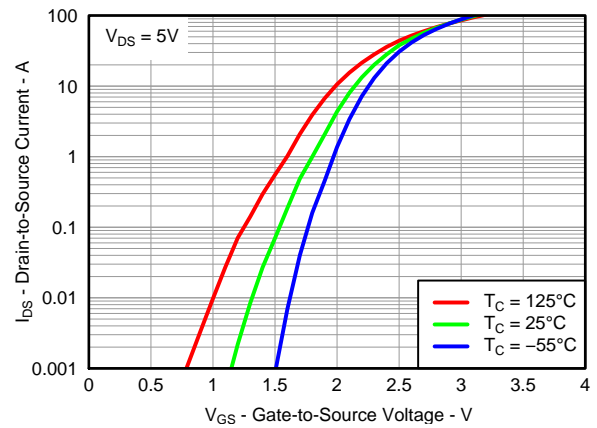
Figure 1. Transient Thermal Impedance

## TYPICAL MOSFET CHARACTERISTICS (continued)

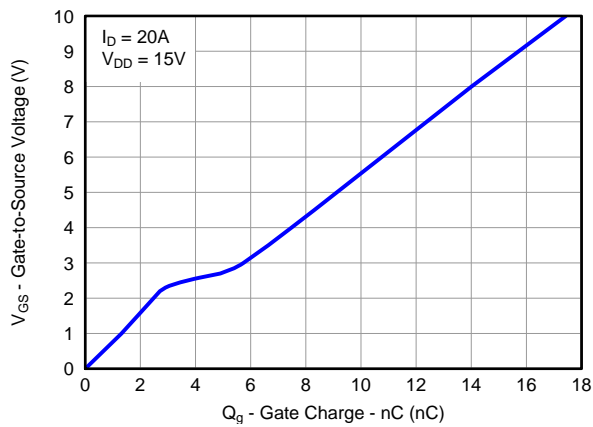
( $T_A = 25^\circ\text{C}$  unless otherwise stated)



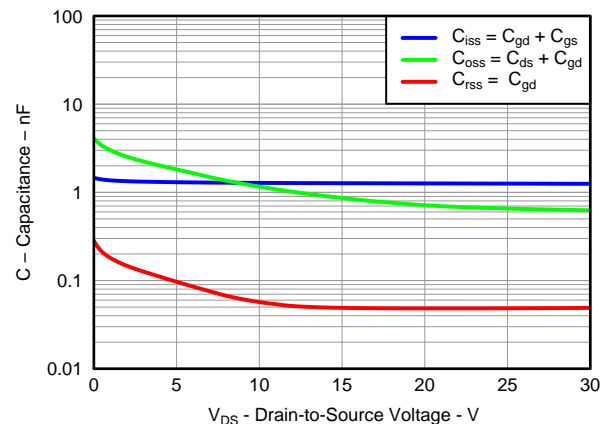
**Figure 2. Saturation Characteristics**



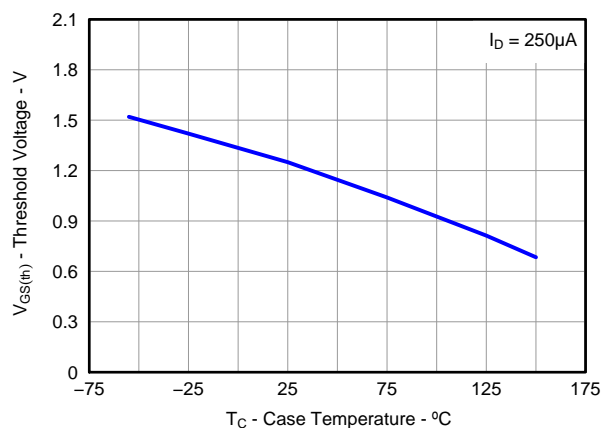
**Figure 3. Transfer Characteristics**



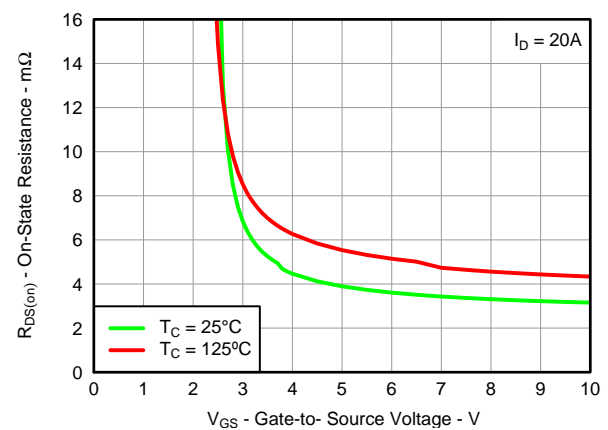
**Figure 4. Gate Charge**



**Figure 5. Capacitance**



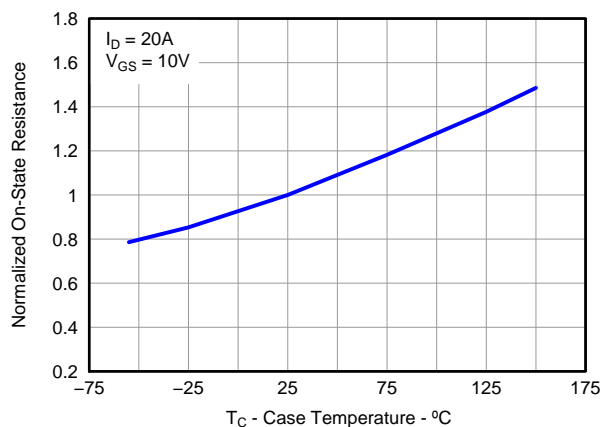
**Figure 6. Threshold Voltage vs. Temperature**



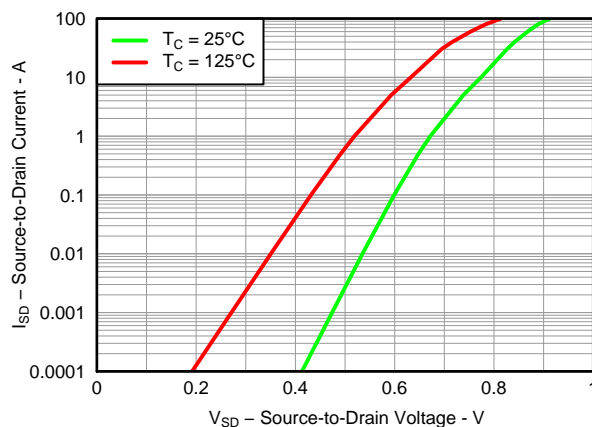
**Figure 7. On-State Resistance vs. Gate-to-Source Voltage**

## TYPICAL MOSFET CHARACTERISTICS (continued)

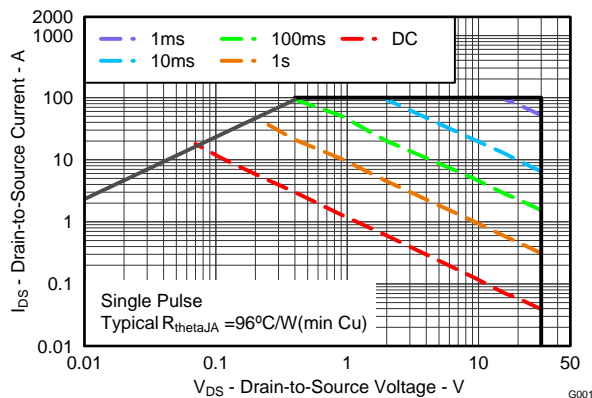
( $T_A = 25^\circ\text{C}$  unless otherwise stated)



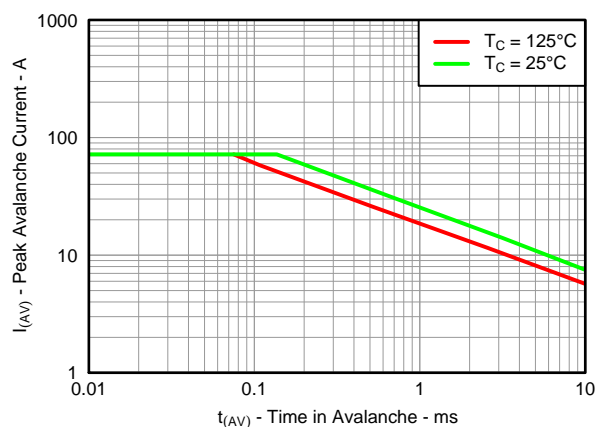
**Figure 8. Normalized On-State Resistance vs. Temperature**



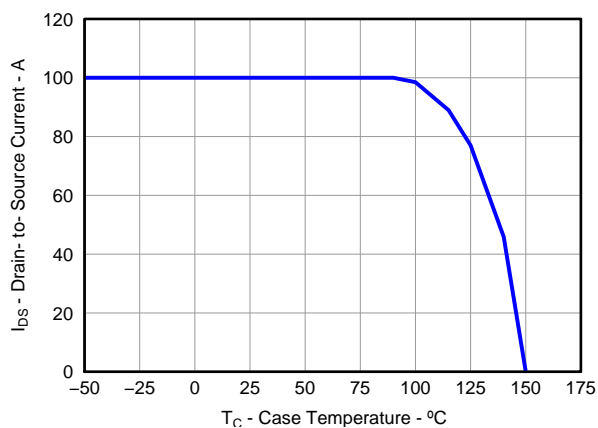
**Figure 9. Typical Diode Forward Voltage**



**Figure 10. Maximum Safe Operating Area**



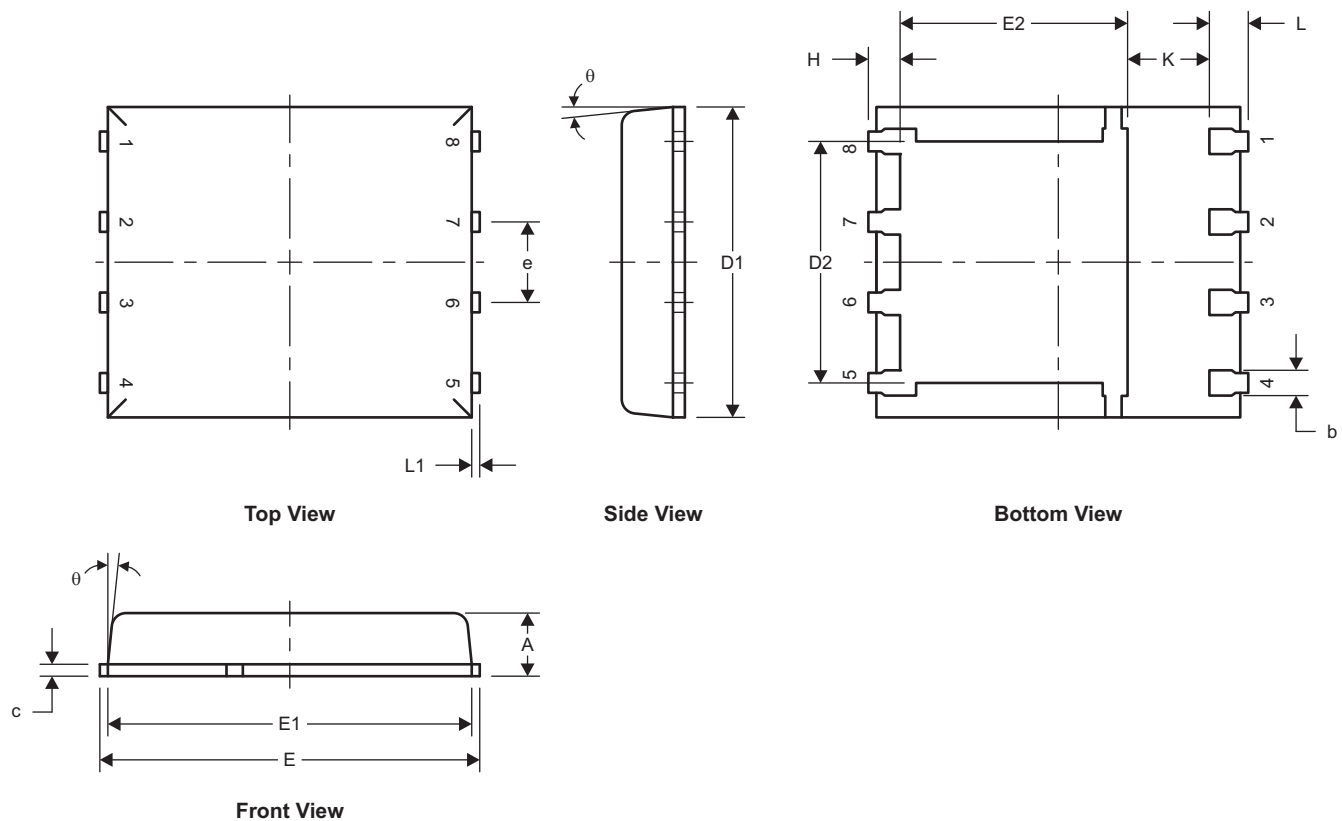
**Figure 11. Single Pulse Unclamped Inductive Switching**



**Figure 12. Maximum Drain Current vs. Temperature**

## MECHANICAL DATA

### Q5A Package Dimensions



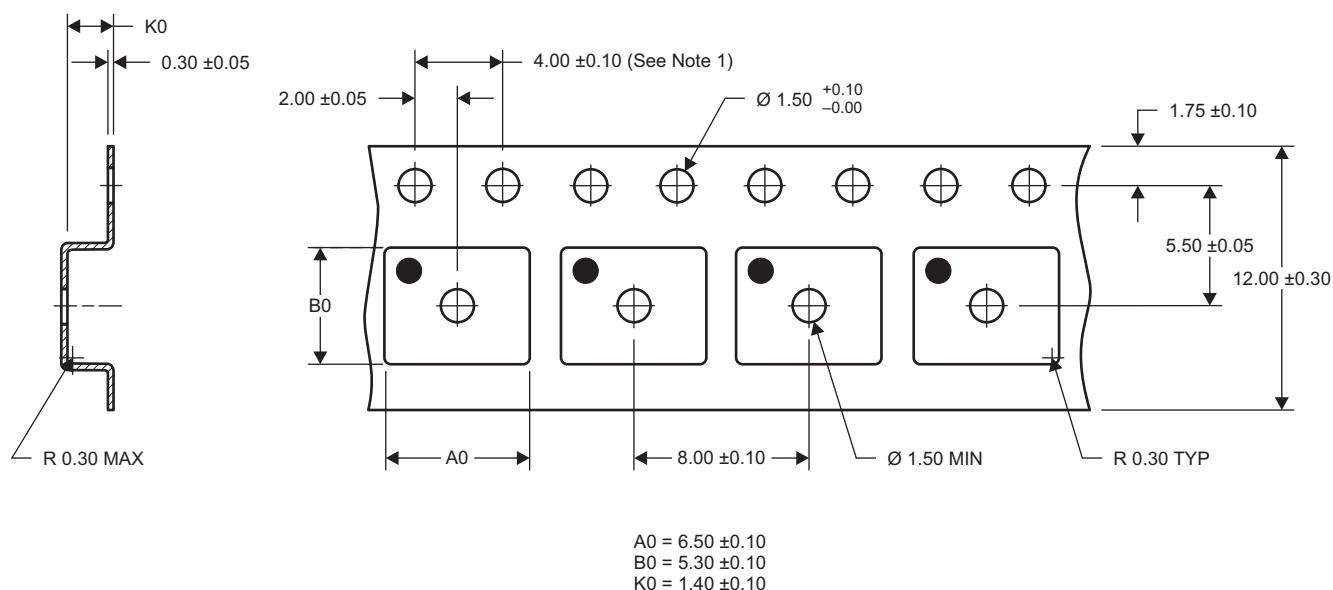
M0135-01

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.41	0.51
c	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.17	1.27	1.37
H	0.41	0.56	0.71
K	1.10		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
$\theta$	0°		12°

NOTE: Dimensions are in mm (inches).

NOTE: Dimensions are in mm (inches).

## Q5A Tape and Reel Information



M0138-01

- NOTES: 1. 10-sprocket hole-pitch cumulative tolerance  $\pm 0.2$
2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified)
5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

## REVISION HISTORY

Changes from Original (December 2010) to Revision A	Page
• Changed $V_{GS}$ in the Abs Max Ratings table From: +20/-12V To: $\pm 20V$ .....	1
• Changed from +20/-12V to 20V .....	2
Changes from Revision A (July 2011) to Revision B	Page
• Changed <a href="#">Figure 10</a> , Maximum Safe Operating Area .....	5



## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD17506Q5A	ACTIVE	VSONP	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD17506	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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DLP® Products	<a href="http://www.dlp.com">www.dlp.com</a>
DSP	<a href="http://dsp.ti.com">dsp.ti.com</a>
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Logic	<a href="http://logic.ti.com">logic.ti.com</a>
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Microcontrollers	<a href="http://microcontroller.ti.com">microcontroller.ti.com</a>
RFID	<a href="http://www.ti-rfid.com">www.ti-rfid.com</a>
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### Applications

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Computers and Peripherals	<a href="http://www.ti.com/computers">www.ti.com/computers</a>
Consumer Electronics	<a href="http://www.ti.com/consumer-apps">www.ti.com/consumer-apps</a>
Energy and Lighting	<a href="http://www.ti.com/energy">www.ti.com/energy</a>
Industrial	<a href="http://www.ti.com/industrial">www.ti.com/industrial</a>
Medical	<a href="http://www.ti.com/medical">www.ti.com/medical</a>
Security	<a href="http://www.ti.com/security">www.ti.com/security</a>
Space, Avionics and Defense	<a href="http://www.ti.com/space-avionics-defense">www.ti.com/space-avionics-defense</a>
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